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over the entire bottom surface of the hollow 14 as shown in Figure 12, the second electrode portion 16b can be made thin in thickness by a corresponding amount to the film thickness of the first electrode portion 16a. This [reduce] reduces the amount of etching to be [conducted] conducted in the etching process.

**IN THE CLAIMS:**

Please cancel Claims 6-14 without prejudice to incorporating the same in a divisional application to be filed.

Please amend Claim 1 by rewriting the same as follows:

1. (Amended) A ferroelectric memory, comprising:  
an insulation film having a hollow at a top surface;  
[a hollow formed in a top surface of said insulation film;]  
a laminated body obtained by laminating a plurality of layers on said top surface and  
etching a region of said plurality of layers corresponding to a region other than said hollow,  
wherein said laminated body includes a lower electrode layer [formed in said hollow;], a  
ferroelectric layer formed on said lower electrode layer [;] and an upper electrode layer  
formed on said ferroelectric layer.

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